

ELECTROSTATIC DISCHARGE INPUT AND POWER CLAMP CIRCUIT FOR HIGH CUT-OFF FREQUENCY TECHNOLOGY RADIO FREQUENCY (RF) APPLICATIONS

Abstract

A SiGe ESD (electrostatic discharge) power clamp circuit having a forward biased trigger device fabricated in a given technology and a clamp transistor preferably comprising a high frequency cutoff SiGe npn transistor, wherein the trigger device has a turn-on voltage which is below the Johnson Limit breakdown voltage of the highest frequency device fabricated in the given technology.